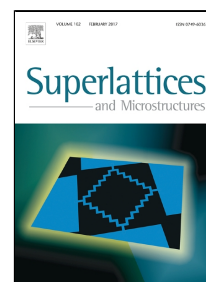


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Different annealing temperature suitable for different Mg doped P-GaN

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Highlight:

- ✧ For first time we present the result that the annealing process not only influences the Mg-acceptors, but also has an impact on the donors in P-GaN.
- ✧ we found that MOCVD-grown GaN with different Mg doping concentration needs a different best annealing temperature.
- ✧ The different annealing tendency of P-GaN with different Mg doped comes from the annealing influence to donors.

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